

Applicant(s): Kee-won Kwon, *et al.*  
U.S. Serial No.: 10/649,850

**Amendments to the Drawings:**

The attached sheet of drawings includes changes to FIGs. 1 and 2. The sheet, which includes FIGs. 1 and 2, replaces the original sheet. FIGs. 1 and 2 are amended to include the legend "Prior Art".

A marked-up version of the drawings, with revisions shown in red, is included with the amended drawings. Entry of the amended drawings is respectfully requested.

Attachment: Replacement Sheet  
Annotated Sheet Showing Changes

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REMARKS

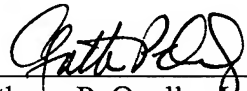
FIGs. 1 and 2 are amended to include the legend "Prior Art" as requested by the Examiner. Acceptance of the amendment to the drawings is respectfully requested.

The present Amendment is directed to matters of form only and does not affect the substance or patentability of the claims.

Therefore, it is requested that the Amendment be entered and that the application be passed to issue. In the event that a telephone conference will expedite prosecution of the application, the Examiner is invited to telephone the undersigned.

Respectfully submitted,

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A cross-sectional view of a semiconductor device. A substrate 10 is shown at the bottom. A layer 40 is formed on the substrate 10. A central cavity 30 is formed in the layer 40. The cavity 30 is defined by a wall 50. A layer 20 is formed on the wall 50. A top layer 60 is formed on the layer 20. A central cavity 70 is formed in the top layer 60. A layer 80 is formed on the top layer 60. The layer 80 is formed on the top layer 60 and the wall 50. The layer 80 is formed on the top layer 60 and the wall 50. The layer 80 is formed on the top layer 60 and the wall 50.